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Electronic Transport in Atomically Abrupt Semiconductor Tunnel Junctions

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In this work we show the results of an atomistic tight-binding approach coupled with the Non-Equilibrium Green's Function (NEGF) formalism when applied to phosphorus doped silicon tunnel junctions that can be manufactured with sub-nanometre accuracy.

Primary authors: DONNELLY, Matthew; MUNIA, Mushita Masud (University of New South Wales); Dr KEIZER, Joris; Dr CHUNG, Yousun; Mr SAFFAT-EE HUQ, A.M.; Ms HSUEH, Yuling; RAHMAN, Rajib (The University of New South Wales); SIMMONS, Michelle (The University of New South Wales)

Presenter: DONNELLY, Matthew

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